

Diode

Fast switching Emitter Controlled 3 diode chip
SIDC14D120H8

Data Sheet

Industrial Power Control



SIDC14D120H8

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Fast switching Emitter Controlled 3 diode chip

Features:

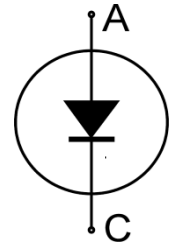
- 1200V Emitter Controlled technology
120µm chip
- Soft, fast switching
- Low reverse recovery charge
- Small temperature coefficient

Recommended for:

- Power modules
- Discrete devices

Applications:

- SMPS
- Resonant applications
- Drives



Chip Type	V_R	I_{Fn}	Die Size	Package
SIDC14D120H8	1200V	25A	3.80mm x 3.80mm	Sawn on foil

Mechanical Parameters

Die size	3.80 x 3.80	mm ²
Area total	14.44	
Anode pad size	See chip drawing	
Silicon thickness	120	µm
Wafer size	200	mm
Maximum possible chips per wafer	1879	
Passivation frontside	Photoimide	
Pad metal	3.2µm AlSiCu	
Backside metal	Ni Ag – system To achieve a reliable solder connection it is strongly recommended not to consume the Ni layer completely during production process	
Die bond	Electrically conductive epoxy glue and soft solder	
Wire bond	Al, ≤ 500µm	
Reject ink dot size (valid for inked delivery form only)	∅ 0.65mm; max 1.2mm	
Storage environment (<6 months)	for original and sealed MBB bags	Ambient atmosphere air, temperature 17°C – 25°C
	for open MBB bags	Acc. IEC 62258-3; Section 9.4 Storage Environment.

Maximum Ratings

In general, from reliability and lifetime point of view, the lower the operation junction temperature and/or the applied voltage, the greater the expected lifetime of any semiconductor device.

Not subject to production test, specified by design.

Parameter	Symbol	Value	Unit
Repetitive peak reverse voltage, $T_{vj} = 25^{\circ}\text{C}$	V_{RRM}	1200	V
Continuous forward current, limited by $T_{vj\max}^1$	I_F	-	A
Maximum repetitive forward current, t_p limited by $T_{vj\max}$	I_{FRM}	50	
Virtual junction temperature	T_{vj}	-40...+175	$^{\circ}\text{C}$

Static Characteristics (tested on wafer), $T_{vj} = 25^{\circ}\text{C}$

Parameter	Symbol	Conditions	Value			Unit
			min.	typ.	max.	
Reverse leakage current	I_R	$V_R = 1200\text{V}$	-	-	20.0	μA
Cathode-anode breakdown voltage	V_{BR}	$I_R = 0.25\text{mA}$	1200	-	-	V
Forward voltage drop	V_F	$I_F = 25\text{A}$	1.23	1.6	1.97	

Electrical Characteristics

Not subject to production test, specified by design.

Parameter	Symbol	Conditions	Value			Unit
			min.	typ.	max.	
Forward voltage drop, $T_{vj} = 125^{\circ}\text{C}$	V_F	$I_F = 25\text{A}$	-	1.65	-	V

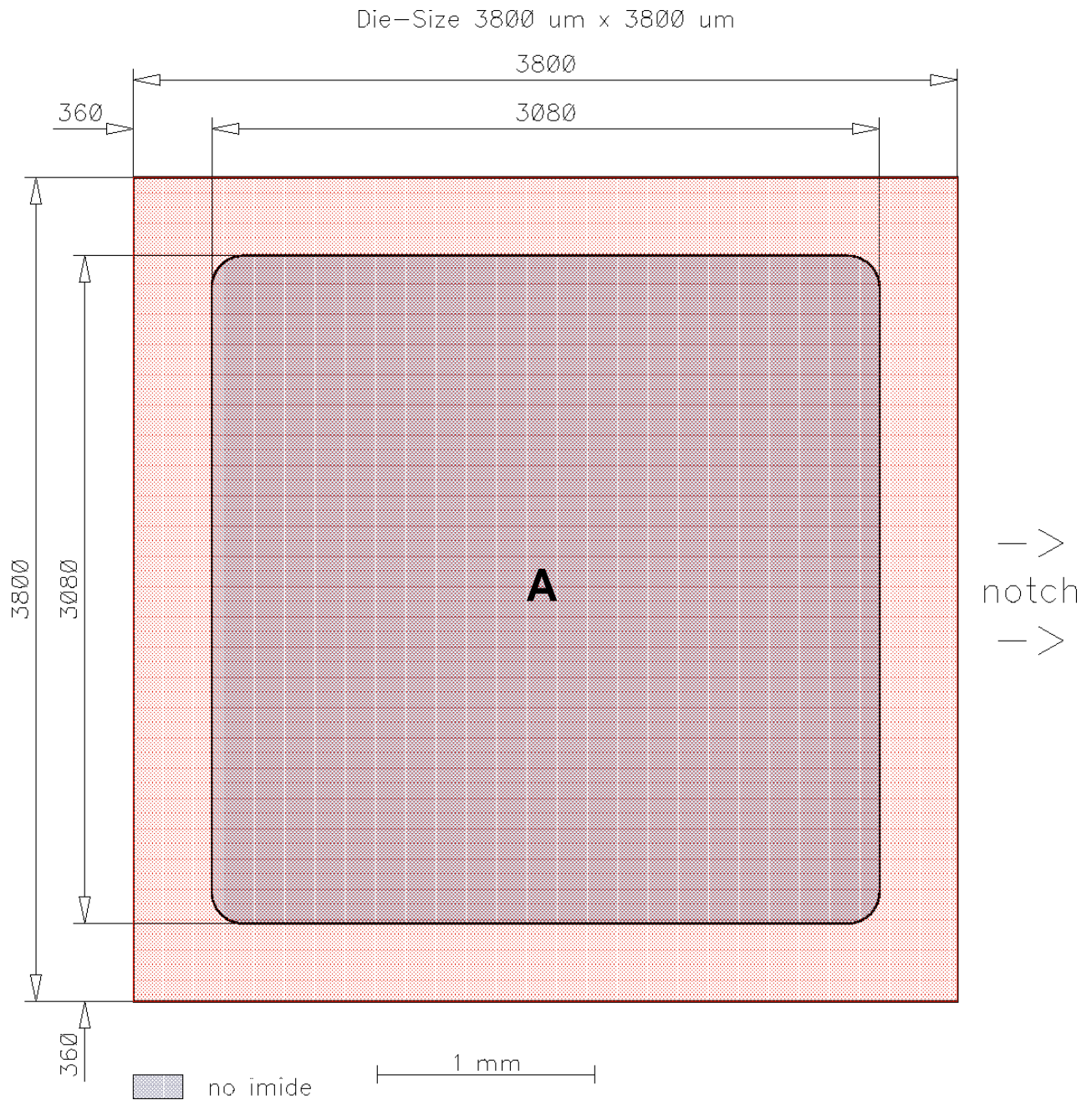
Further Electrical Characteristics

Switching characteristics and thermal properties are depending strongly on module design and mounting technology and can therefore not be specified for a bare die.

Application example	FP25R12KE3	Rev. 3.0
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¹ Depending on thermal properties of assembly.

Chip Drawing



A = Anode pad

Bare Die Product Specifics

Test coverage at wafer level cannot cover all application conditions. Therefore it is recommended to test all characteristics which are relevant for the application at package level, including RBSOA and SCSOA.

Description

AQL 0.65 for visual inspection according to failure catalogue

Electrostatic Discharge Sensitive Device according to MIL-STD 883

Revision History

Revision	Subjects (major changes since last revision)	Date
2.0	Final data sheet	26.10.2012
2.1	Operating junction temperature	15.05.2013
2.2	Editorial changes	14.10.2015
2.3	$I_F + I_{FRM}$ conditions changed, T_{vj} increased to 175°C, editorial changes	23.12.2021



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